

RoHS

HALOGEN

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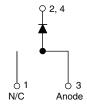
HEXFRED®, Ultrafast Soft Recovery Diode, 4 A



TO-252AA (D-PAK)

T_J max.

Diode variation



150 °C

Single die

PRODUCT SUMMARY					
Package	TO-252AA (D-PAK)				
I _{F(AV)}	4 A				
V_{R}	600 V				
V _F at I _F	1.4 V				
t _{rr} typ.	17 ns				

FEATURES



- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V_{RRM}		600	V			
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4				
Single pulse forward current	I _{FSM}		25	Α			
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16				
Maximum power dissipation	P _D	T _C = 100 °C	10	W			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Forward voltage See fig. 1	V _F	I _F = 4 A	-	1.5	1.8	V	
		I _F = 8 A	-	1.8	2.2		
		I _F = 4 A, T _J = 125 °C	-	1.4	1.7		
Maximum reverse		V _R = V _R rated	-	0.17	3.0		
leakage current	I _R	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	44	300	μA	
Junction capacitance	C _T	V _R = 200 V	-	4	8	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	





DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
			I _F = 1.0 A, dI _F /dt = 200 A/μA, V _R = 30 V		17	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns	
		T _J = 125 °C		-	38	57		
Dools recovery average	I _{RRM}	T _J = 25 °C		-	2.9	5.2	^	
Peak recovery current		IRRM	T _J = 125 °C	$I_F = 4 \text{ A}$	-	3.7	6.7	А
Poverse recovery charge	0	T _J = 25 °C	dl _F /dt = 200 A/μs V _B = 200 V	-	40	60	nC	
Reverse recovery charge	Q_{rr}	Q _{rr}	T _J = 125 °C		-	70	105	IIC
Rate of fall of recovery current	dl _{(rec)M} /dt	-11 /-11	T _J = 25 °C		-	280	-	Λ/μο
		T _J = 125 °C		-	235	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- C/VV	
Majaht			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-252AA (D-PAK)	HFA04SD60S				

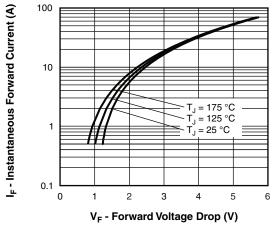


Fig. 1 - Typical Forward Voltage Drop Characteristics

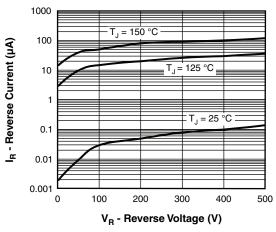


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

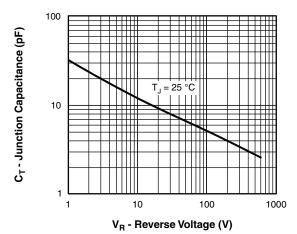


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

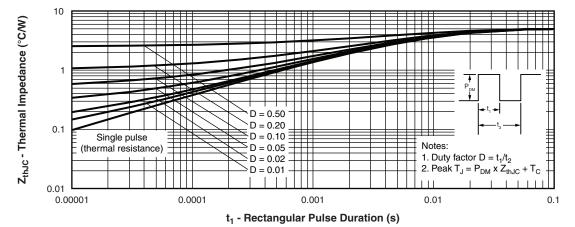


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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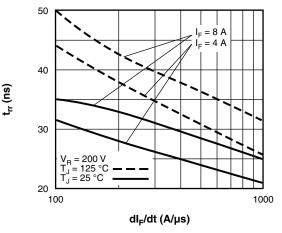


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

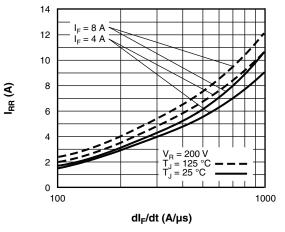


Fig. 6 - Typical Recovery Current vs. dl_F/dt

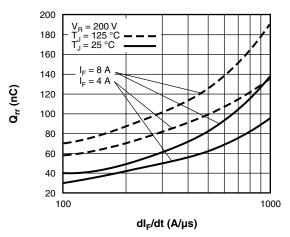


Fig. 7 - Typical Stored Charge vs. dl_F/dt

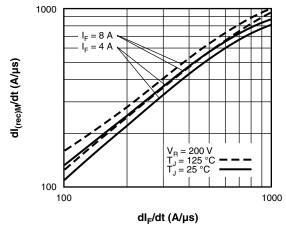


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

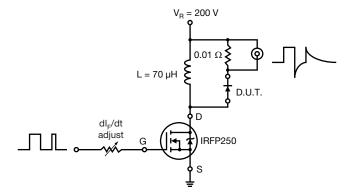
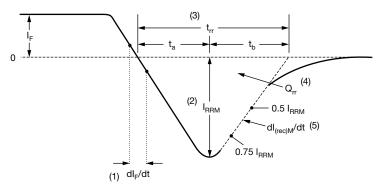


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

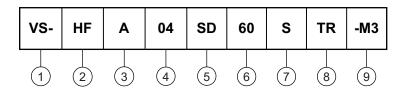
(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

Current rating (04 = 4 A)

5 - D-PAK

Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = tape and reel

• R = tape and reel (right oriented)

• L = tape and reel (left oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

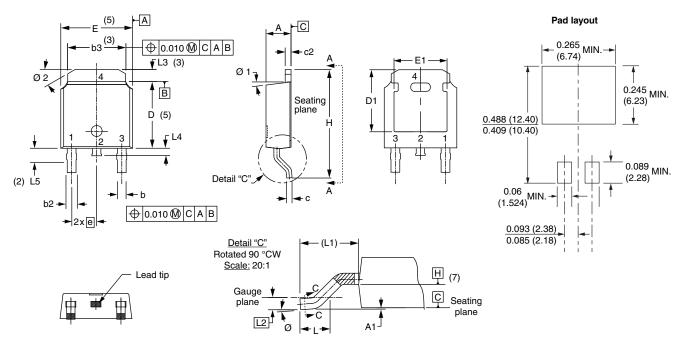
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA04SD60S-M3	75	3000	Antistatic plastic tube				
VS-HFA04SD60STR-M3	2000	2000	13" diameter reel				
VS-HFA04SD60SL-M3	3000	3000	13" diameter reel				
VS-HFA04SD60SR-M3	3000	3000	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95627				
Part marking information	www.vishay.com/doc?95176				
Packaging information	www.vishay.com/doc?95033				



D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	2.18	2.39	0.086	0.094		
A1	-	0.13	-	0.005		
b	0.64	0.89	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215	3	
С	0.46	0.61	0.018	0.024		
c2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245	5	
D1	5.21	-	0.205	-	3	
Е	6.35	6.73	0.250	0.265	5	
E1	4.32	-	0.170	-	3	

SYMBOL	MILLIMETERS INCHES		NOTES		
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29	BSC	0.090	BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51	BSC	0.020	0.020 BSC	
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0°	10°	
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC® outline TO-252AA



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